



## P-Channel 20-V (D-S) MOSFET

| PRODUCT SUMMARY     |                                      |                    |  |  |  |
|---------------------|--------------------------------------|--------------------|--|--|--|
| V <sub>DS</sub> (V) | $R_{DS(on)}\left(\Omega\right)$      | I <sub>D</sub> (A) |  |  |  |
|                     | 0.00875 at V <sub>GS</sub> = - 4.5 V | - 14               |  |  |  |
| - 20                | 0.01075 at V <sub>GS</sub> = - 2.5 V | - 12               |  |  |  |
|                     | 0.0135 at V <sub>GS</sub> = - 1.8 V  | - 11               |  |  |  |

#### **FEATURES**

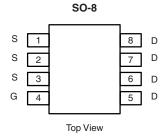
- Halogen-free Option Available
- TrenchFET® Power MOSFET

## Pb-free

RoHS

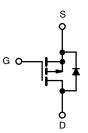
#### **APPLICATIONS**

- · Game Station
  - Load Switch



Ordering Information: Si4421DY-T1-E3 (Lead (Pb)-free)

Si4421DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

| <b>ABSOLUTE MAXIMUM RATINGS</b> T <sub>A</sub> = 25 °C, unless otherwise noted |                                   |                  |              |        |   |  |
|--|-----------------------------------|------------------|--------------|--------|---|--|
| Parameter  | Symbol                            | 10 s             | Steady State | Unit   |   |  |
| Drain-Source Voltage   |                                   | V <sub>DS</sub>  | - 20         |        | V |  |
| Gate-Source Voltage  |                                   | $V_{GS}$         | ± 8          |        |   |  |
| Continuous Drain Current (T <sub>.I</sub> = 150 °C) <sup>a</sup>               | T <sub>A</sub> = 25 °C            | - I <sub>D</sub> | - 14         | - 10   | A |  |
| Continuous Diam Current (1) = 150 °C)  | T <sub>A</sub> = 70 °C            |                  | - 11.5       | - 8    |   |  |
| Pulsed Drain Current   |                                   | I <sub>DM</sub>  | - 40         |        | A |  |
| Continuous Source Current (Diode Conduction) <sup>a</sup>                      |                                   | I <sub>S</sub>   | - 2.7        | - 1.36 |   |  |
| Maximum Power Dissipation <sup>a</sup>   | T <sub>A</sub> = 25 °C            | P <sub>D</sub>   | 3.0          | 1.5    | W |  |
| waxiinani i owei Dissipation   | T <sub>A</sub> = 70 °C            |                  | 1.9          | 0.95   |   |  |
| Operating Junction and Storage Temperature Range                               | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150      |              | °C     |   |  |

| THERMAL RESISTANCE RATINGS               |              |                   |         |      |      |
|--|--------------|-------------------|---------|------|------|
| Parameter                                | Symbol       | Typical           | Maximum | Unit |      |
| Manipana lugation to Ambienti            | t ≤ 10 s     | R <sub>thJA</sub> | 33      | 42   | °C/W |
| Maximum Junction-to-Ambient <sup>a</sup> | Steady State |                   | 70      | 85   |      |
| Maximum Junction-to-Foot (Drain)         | Steady State | $R_{thJF}$        | 16      | 21   |      |

#### Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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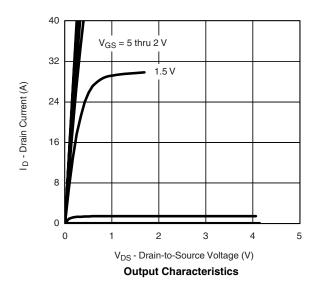
| Parameter                                     | Symbol   | Test Conditions  | Min.  | Тур.   | Max.    | Unit |  |
|---|--|--|-------|--------|---------|------|--|
| Static  |  |  | •     |        |         |      |  |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub>                                  | $V_{DS} = V_{GS}, I_{D} = -850 \mu\text{A}$                              | - 0.4 |        | - 0.8   | V    |  |
| Gate-Body Leakage                             | I <sub>GSS</sub>                                     | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$                         |       |        | ± 100   | nA   |  |
| 7 0   |  | $V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$                           |       |        | - 1     |      |  |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>                                     | $V_{DS}$ = - 20 V, $V_{GS}$ = 0 V, $T_J$ = 70 °C                         |       |        | - 10    | μΑ   |  |
| On-State Drain Current <sup>a</sup>           | I <sub>D(on)</sub>                                   | V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 4.5 V                       | - 30  |        |         | Α    |  |
|   |  | V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 14 A                       |       | 0.007  | 0.00875 |      |  |
| Drain-Source On-State Resistance <sup>a</sup> | R <sub>DS(on)</sub>                                  | $V_{GS} = -2.5 \text{ V}, I_D = -12 \text{ A}$                           |       | 0.0085 | 0.01075 | Ω    |  |
|   |  | $V_{GS} = -1.8 \text{ V}, I_D = -11 \text{ A}$                           |       | 0.011  | 0.0135  |      |  |
| Forward Transconductance <sup>a</sup>         | 9 <sub>fs</sub>                                      | V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 14 A                        |       | 55     |         | S    |  |
| Diode Forward Voltage <sup>a</sup>            | V <sub>SD</sub>                                      | $I_S = -2.7 \text{ A}, V_{GS} = 0 \text{ V}$                             |       | - 0.6  | - 1.1   | V    |  |
| Dynamic <sup>b</sup>                          |  |  | •     | •      |         |      |  |
| Total Gate Charge                             | $Q_g$  |  |       | 82     | 125     |      |  |
| Gate-Source Charge                            | Q <sub>gs</sub>                                      | $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -14 \text{ A}$ |       | 10     |         | nC   |  |
| Gate-Drain Charge                             | Q <sub>gd</sub>                                      |  |       | 27     |         |      |  |
| Gate Resistance                               | $R_{g}$  |  |       | 3      |         | Ω    |  |
| Turn-On Delay Time                            | t <sub>d(on)</sub>                                   |  |       | 45     | 70      |      |  |
| Rise Time                                     | t <sub>r</sub>                                       | $V_{DD}$ = - 10 V, $R_L$ = 10 $\Omega$                                   |       | 90     | 140     |      |  |
| Turn-Off Delay Time                           | t <sub>d(off)</sub> I <sub>E</sub>                   | $I_D \cong$ - 1 A, $V_{GEN}$ = - 4.5 V, $R_G$ = 6 $\Omega$               |       | 350    | 550     | ns   |  |
| Fall Time                                     | t <sub>f</sub>                                       |  |       | 170    | 260     | 113  |  |
| Source-Drain Reverse Recovery Time            | - I I <sub>rr</sub> I IE = - 2.1 A. UI/UI = 100 A/US |  |       | 135    | 210     |      |  |

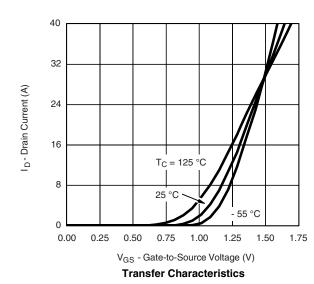
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

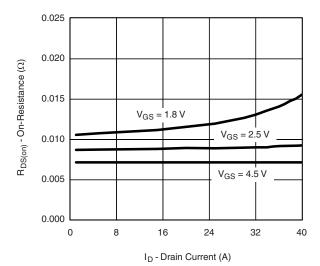
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



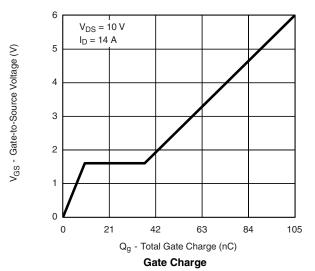


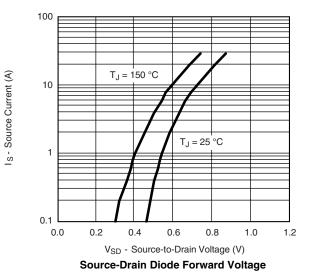


#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



#### On-Resistance vs. Drain Current

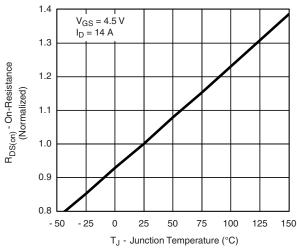




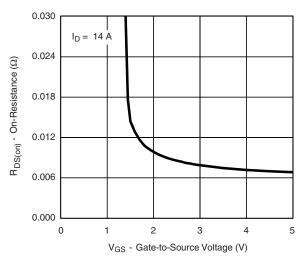
10 000 8000 C<sub>iss</sub> 4000 2000 C<sub>rss</sub> C<sub>oss</sub> 10 12

V<sub>DS</sub> - Drain-to-Source Voltage (V)

#### Capacitance



On-Resistance vs. Junction Temperature

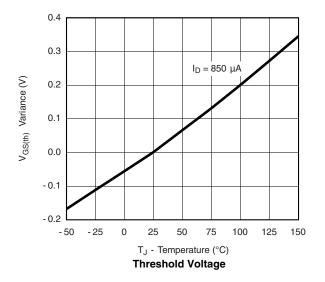


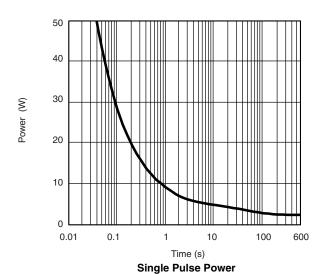
On-Resistance vs. Gate-to-Source Voltage

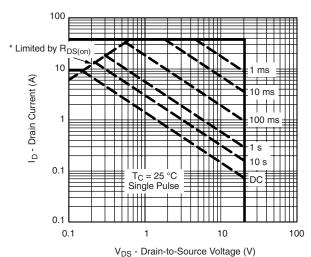
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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

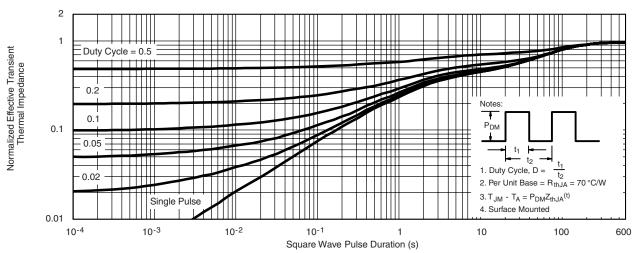






\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

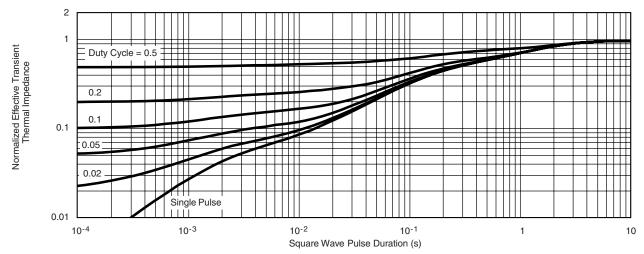
#### Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?72114">http://www.vishay.com/ppg?72114</a>.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







|                              | MILLIMETERS INCHES |      |           | HES   |  |
|------------------------------|--------------------|------|-----------|-------|--|
| DIM                          | Min                | Max  | Min       | Max   |  |
| Α                            | 1.35               | 1.75 | 0.053     | 0.069 |  |
| A <sub>1</sub>               | 0.10               | 0.20 | 0.004     | 0.008 |  |
| В                            | 0.35               | 0.51 | 0.014     | 0.020 |  |
| С                            | 0.19               | 0.25 | 0.0075    | 0.010 |  |
| D                            | 4.80               | 5.00 | 0.189     | 0.196 |  |
| E                            | 3.80               | 4.00 | 0.150     | 0.157 |  |
| е                            | 1.27 BSC           |      | 0.050 BSC |       |  |
| Н                            | 5.80               | 6.20 | 0.228     | 0.244 |  |
| h                            | 0.25               | 0.50 | 0.010     | 0.020 |  |
| L                            | 0.50               | 0.93 | 0.020     | 0.037 |  |
| q                            | 0°                 | 8°   | 0°        | 8°    |  |
| S                            | 0.44               | 0.64 | 0.018     | 0.026 |  |
| FCN: C-06527-Bey   11-Sen-06 |                    |      |           |       |  |

DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06



#### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

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